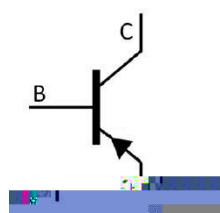


Silicon PNP transistor in a SOT-23 Plastic Package.

High h_{FE} , complementary pair with 2SC5344S.

Audio power amplifier application.

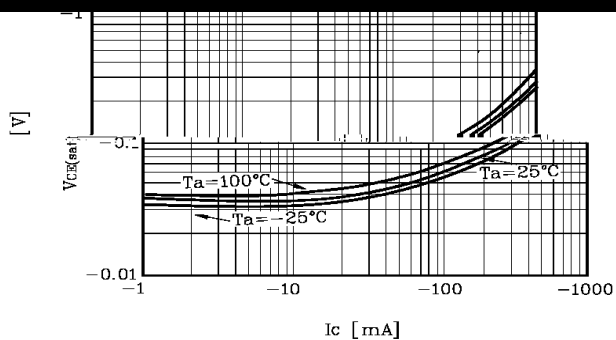
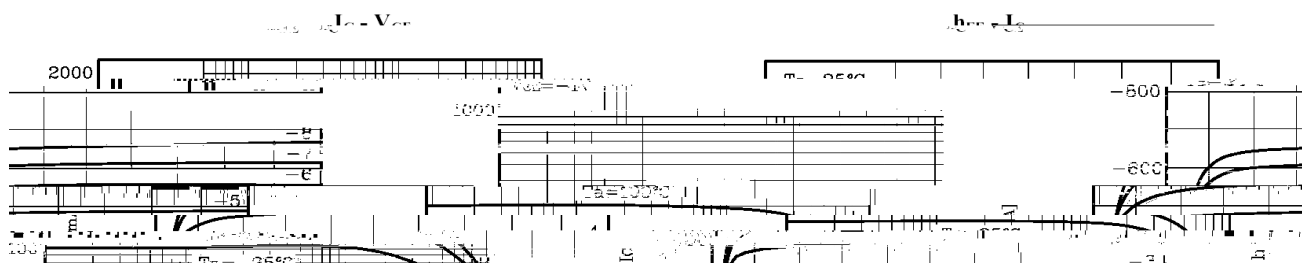
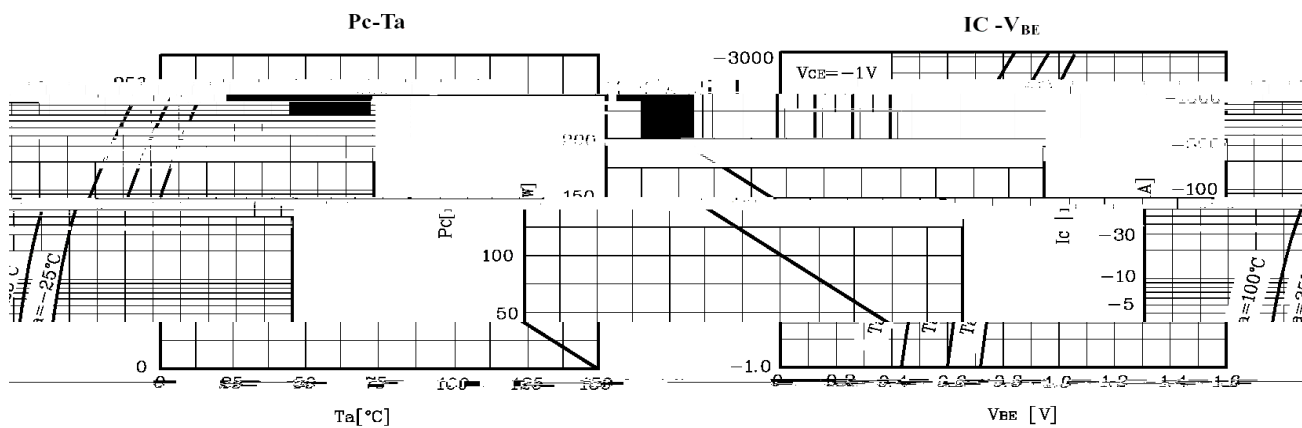


PIN1	Base	PIN 2	Emitter	PIN 3	Collector					
9	3	2	1	0	.	5	0	0	1	0

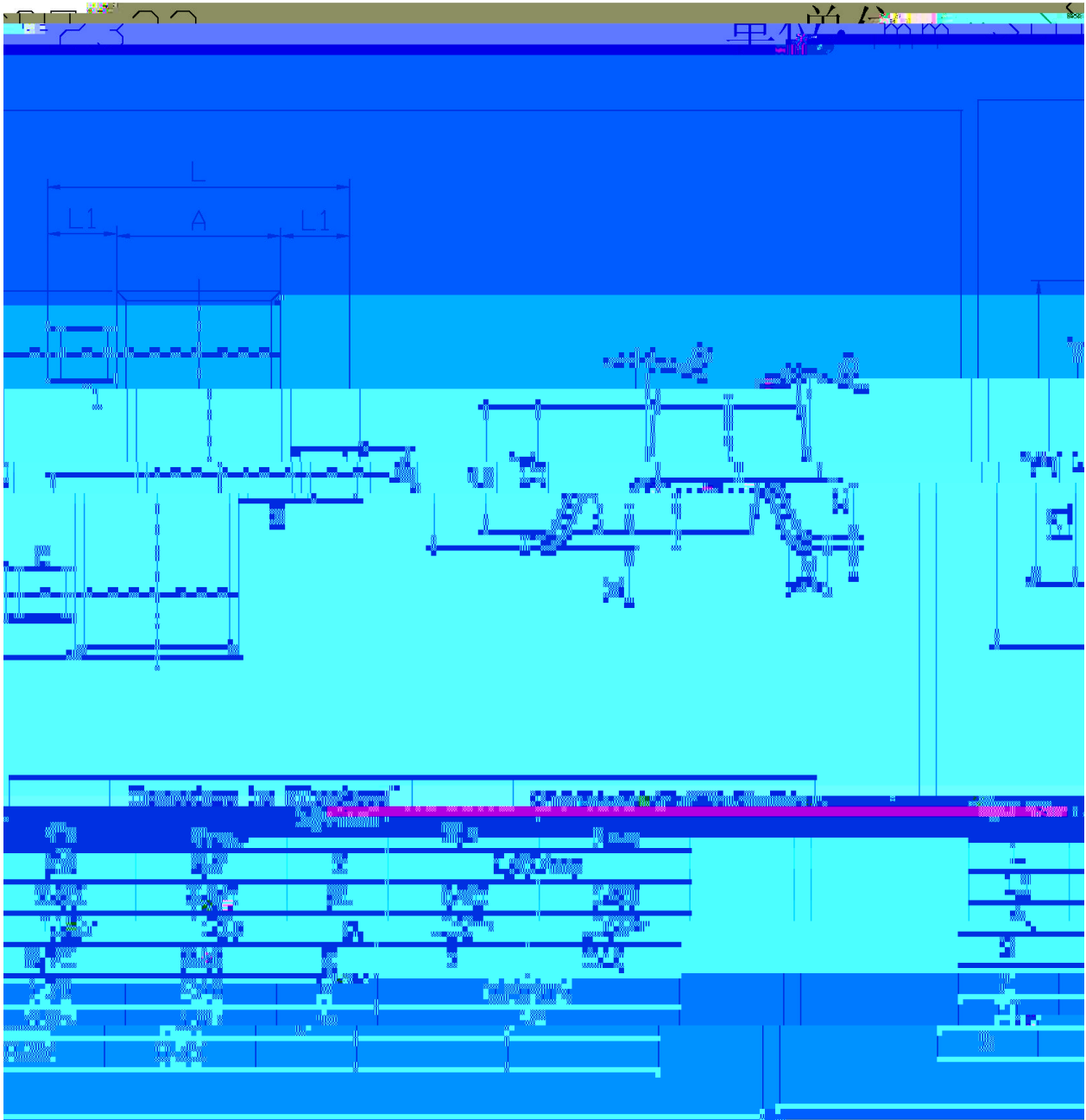
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-35	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-800	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	V_{CBO}	$I_C = -500\mu A$ $I_E = 0$	-35			V
Collector-Emitter breakdown Voltage	V_{CEO}	$I_C = -1.0mA$ $I_B = 0$	-30			V
Emitter-Base Breakdown Voltage	V_{EBO}	$I_E = -50\mu A$ $I_C = 0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -35V$ $I_E = 0$			-0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB} = -5.0V$ $I_C = 0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = -1.0V$ I				

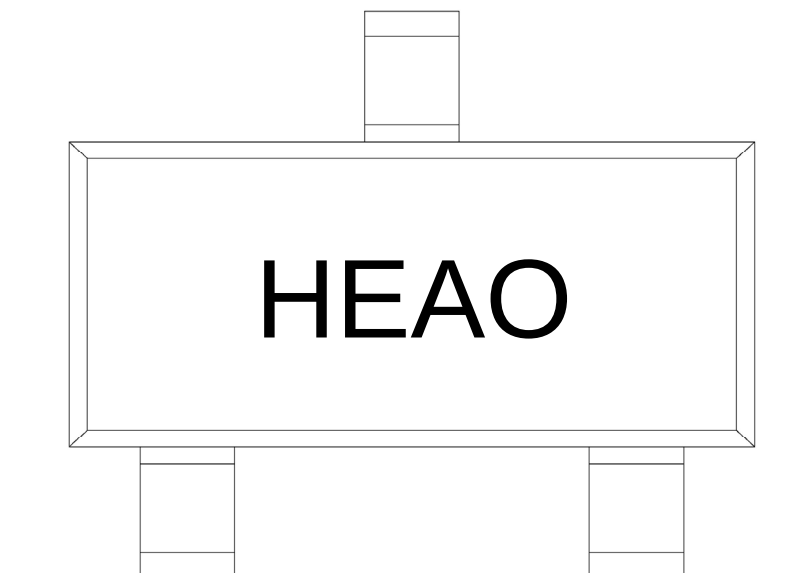
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



h_{FE}

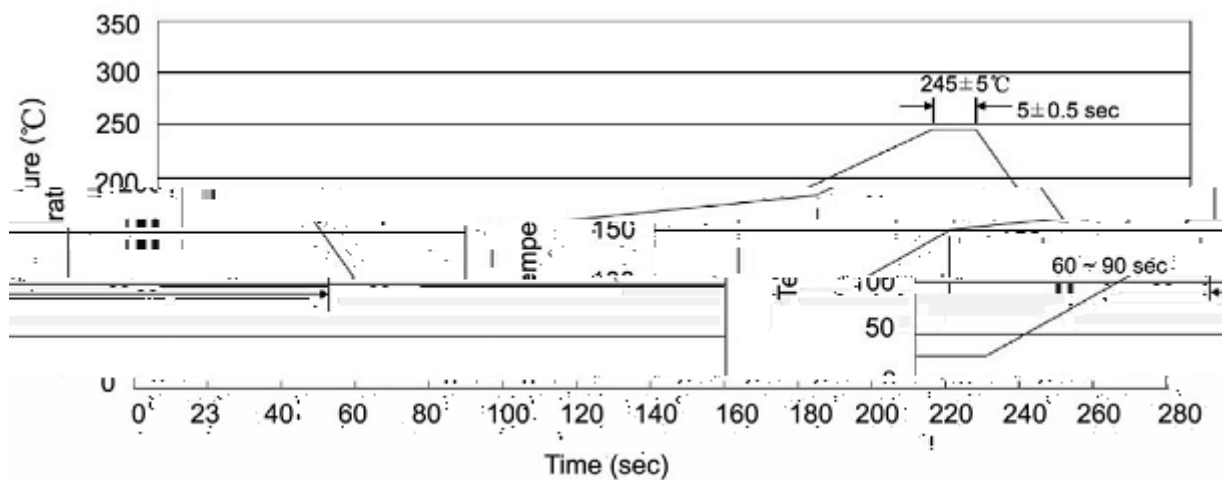
Note:

H: Company Code.

EA: Product Type Code

O: h_{FE} Classifications Symbol Code

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1 25 150 60